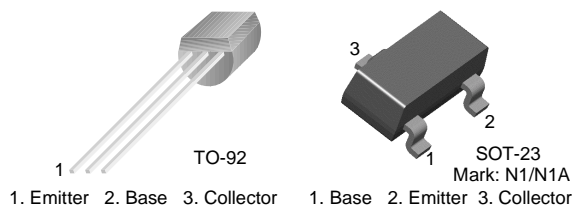


## PN100/PN100A/MMBT100/MMBT100A

### NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at collector currents to 300mA.
- Sourced from process 10.



### Absolute Maximum Ratings\* $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                        | Value      | Units            |
|----------------|----------------------------------|------------|------------------|
| $V_{CEO}$      | Collector-Emitter Voltage        | 45         | V                |
| $V_{CBO}$      | Collector-Base Voltage           | 75         | V                |
| $V_{EBO}$      | Emitter-Base Voltage             | 6.0        | V                |
| $I_C$          | Collector current - Continuous   | 500        | mA               |
| $T_J, T_{stg}$ | Junction and Storage Temperature | -55 ~ +150 | $^\circ\text{C}$ |

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- These ratings are based on a maximum junction temperature of 150 degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol                              | Parameter                             | Test Condition  | Min.                                      | Max.  | Units    |
|-------------------------------------|---------------------------------------|---|---|---|----------|
| <b>Off Characteristics</b>          |                                       |   |   |   |          |
| $BV_{CBO}$                          | Collector-Base Breakdown Voltage      | $I_C = 10\mu\text{A}, I_B = 0$  | 75  |   | V        |
| $BV_{CEO}$                          | Collector-Emitter Breakdown Voltage * | $I_C = 1\text{mA}, I_E = 0$   | 45  |   | V        |
| $BV_{EBO}$                          | Emitter-Base Breakdown Voltage        | $I_C = 10\mu\text{A}, I_C = 0$  | 6.0                                       |   | V        |
| $I_{CBO}$                           | Emitter Cutoff Current                | $V_{CB} = 60\text{V}$   |   | 50  | nA       |
| $I_{CES}$                           | Collector Cutoff Current              | $V_{CE} = 40\text{V}$   |   | 50  | nA       |
| $I_{EBO}$                           | Emitter Cutoff Current                | $V_{EB} = 4\text{V}$  |   | 50  | nA       |
| <b>On Characteristics</b>           |                                       |   |   |   |          |
| $h_{FE}$                            | DC Current Gain                       | $I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$<br>$I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$<br>$I_C = 100\text{mA}, V_{CE} = 1.0\text{V}^*$<br>$I_C = 150\text{mA}, V_{CE} = 5.0\text{V}^*$ | 100<br>100A<br>100<br>100A<br>100<br>100A | 80<br>240<br>100<br>300<br>100<br>100<br>350<br>100 |          |
| $V_{CE(sat)}$                       | Collector-Emitter Saturation Voltage  | $I_C = 10\text{mA}, I_B = 1.0\text{mA}$<br>$I_C = 200\text{mA}, I_B = 20\text{mA}$  |   | 0.2<br>0.4  | V<br>V   |
| $V_{BE(sat)}$                       | Base-Emitter Saturation Voltage       | $I_C = 10\text{mA}, I_B = 1.0\text{mA}$<br>$I_C = 200\text{mA}, I_B = 20\text{mA}$  |   | 0.85<br>1.0   | V<br>V   |
| <b>Small Signal Characteristics</b> |                                       |   |   |   |          |
| $f_T$                               | Current Gain Bandwidth Product        | $V_{CE} = 20\text{V}, I_C = 20\text{mA}$  | 250                                       |   | MHz      |
| $C_{obo}$                           | Output Capacitance                    | $V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}$   |   | 4.5   | pF       |
| NF                                  | Noise Figure                          | $I_C = 100\mu\text{A}, V_{CE} = 5.0\text{V}$<br>$R_G = 2.0\text{k}\Omega, f = 1.0\text{KHz}$  | 100<br>100A                               | 5.0<br>4.0  | dB<br>dB |

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**Thermal Characteristics**  $T_A=25^{\circ}\text{C}$  unless otherwise noted

| Symbol          | Parameter                               | Max.            |                       | Units |
|-----------------|---|-----------------|-----------------------|-------|
|                 |   | PN100<br>PN100A | *MMBT100<br>*MMBT100A |       |
| $P_D$           | Total Device Dissipation                | 625             | 350                   | mW    |
|                 | Derate above 25°C                       | 5.0             | 2.8                   | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 83.3            |                       | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200             | 357                   | °C/W  |

\* Device mounted on FR-4 PCB 1.6" x 1.6" x 0.06."

# Typical Characteristics

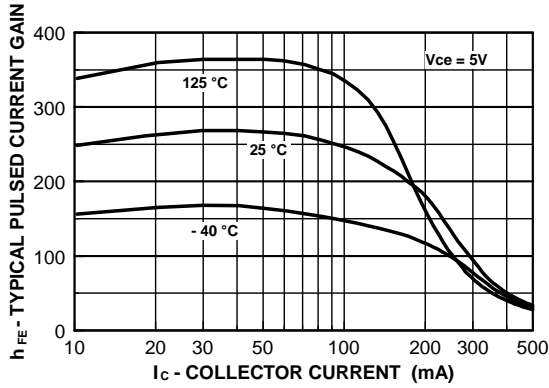


Figure 1. Typical Pulsed Current Gain vs Collector Current

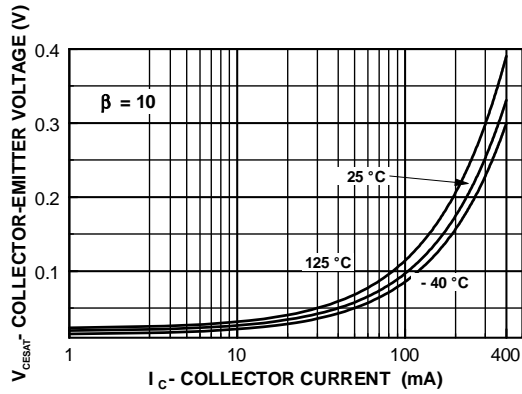


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

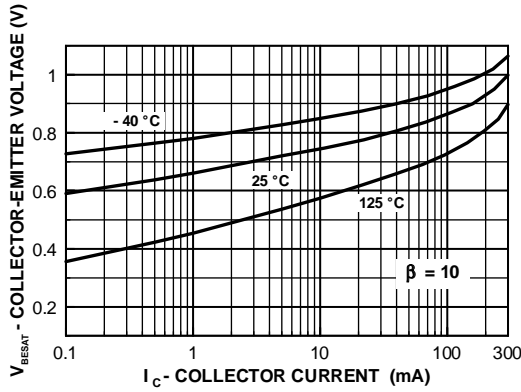


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

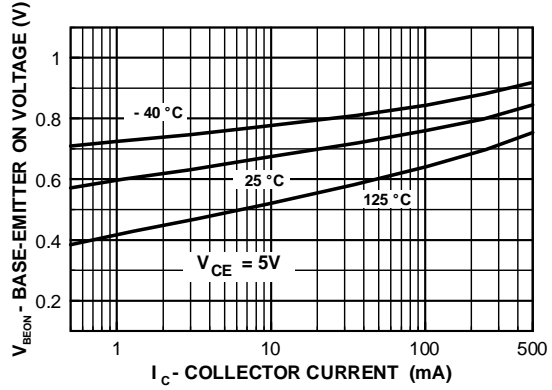


Figure 4. Base-Emitter On Voltage vs Collector Current

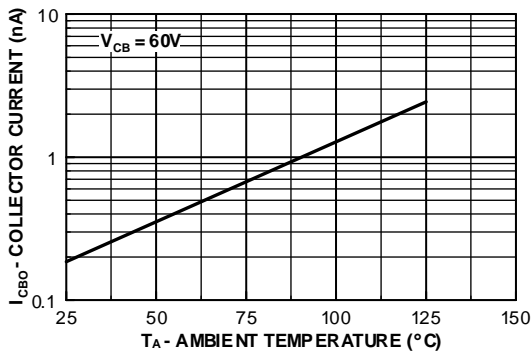


Figure 5. Collector Cutoff Current vs Ambient Temperature

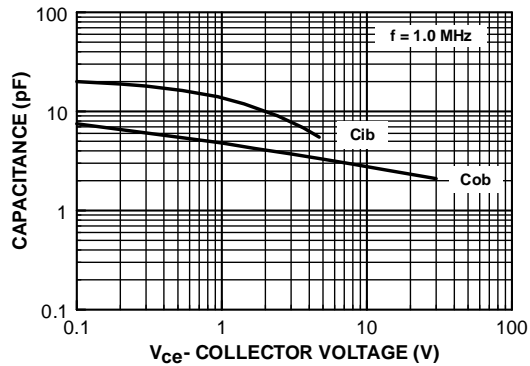


Figure 6. Input and Output Capacitance vs Reverse Voltage

## Typical Characteristics (Continued)

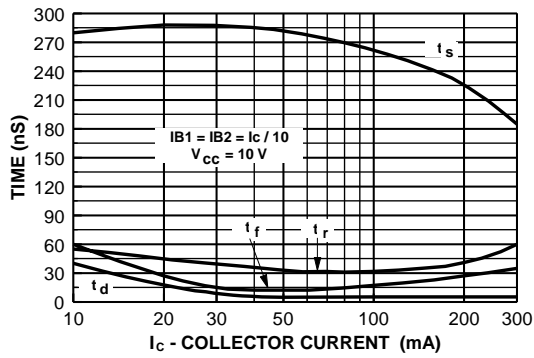


Figure 7. Switching Times vs Collector Current

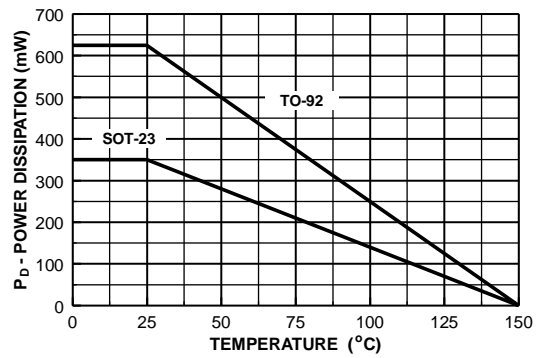
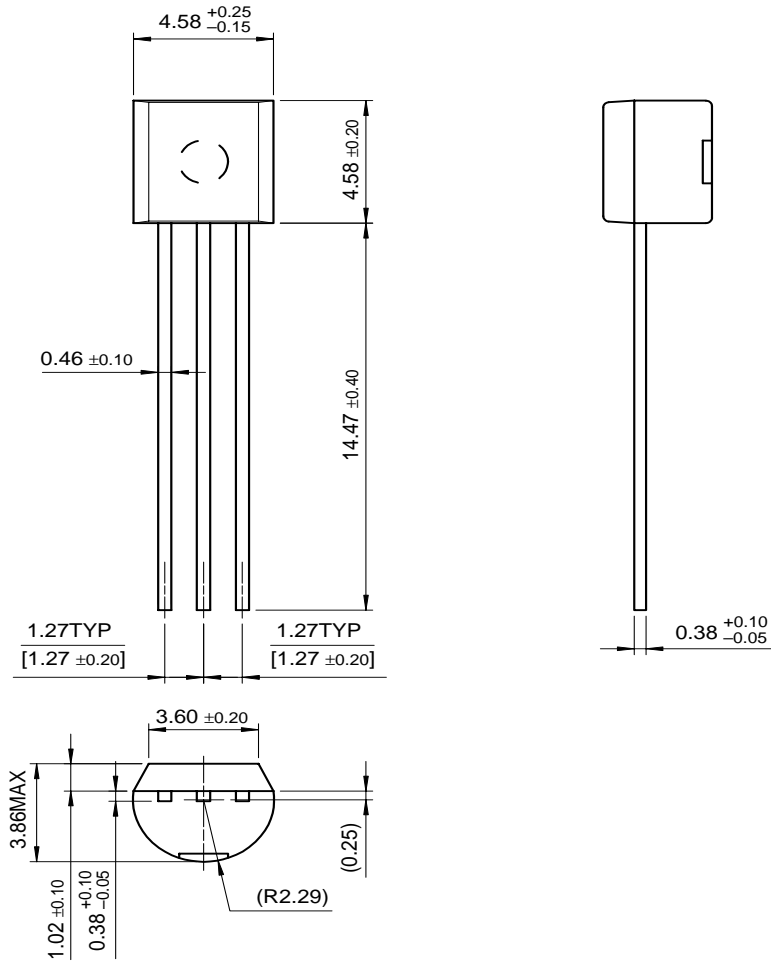


Figure 8. Power Dissipation vs Ambient Temperature

PN100/PN100A/MMBT100/MMBT100A

# Package Dimensions

## TO-92

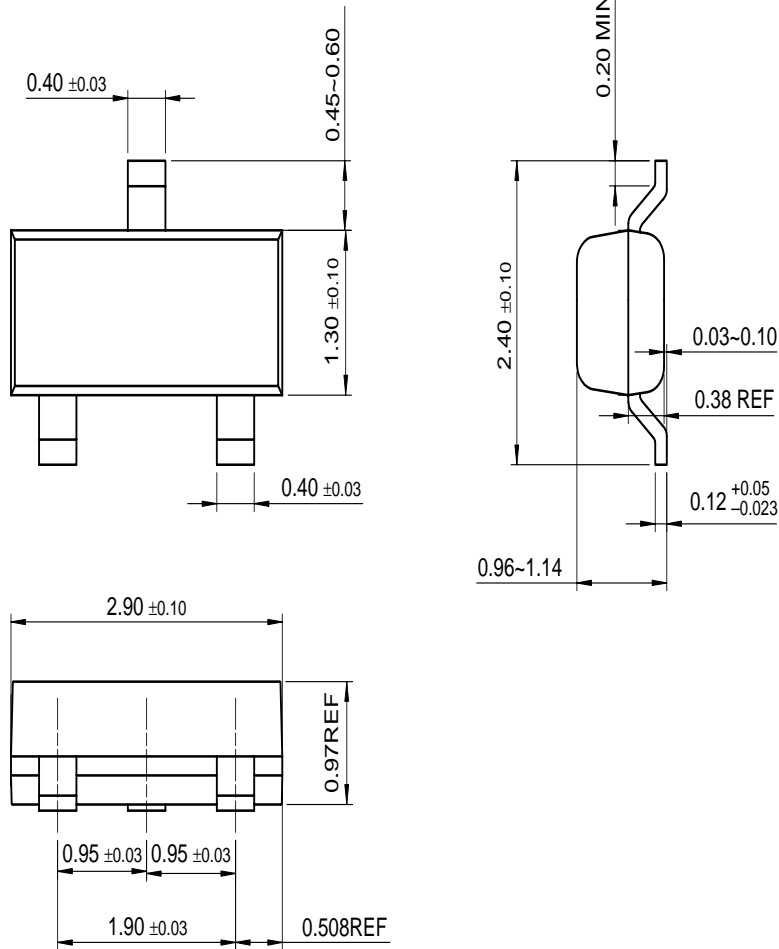


PN100/PN100A/MMBT100/MMBT100A

Dimensions in Millimeters

# Package Dimensions (Continued)

## SOT-23



PN100/PN100A/MMBT100/MMBT100A

Dimensions in Millimeters

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| Bottomless <sup>™</sup>                          | FAST <sup>®</sup>               | LittleFET <sup>™</sup>         | Power247 <sup>™</sup>           | SuperSOT <sup>™</sup> -3    |
| CoolFET <sup>™</sup>                             | FAST <sup>™</sup>               | MicroFET <sup>™</sup>          | PowerTrench <sup>®</sup>        | SuperSOT <sup>™</sup> -6    |
| CROSSVOLT <sup>™</sup>                           | FRFET <sup>™</sup>              | MicroPak <sup>™</sup>          | QFET <sup>™</sup>               | SuperSOT <sup>™</sup> -8    |
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| EcoSPARK <sup>™</sup>                            | GTO <sup>™</sup>                | MSX <sup>™</sup>               | QT Optoelectronics <sup>™</sup> | TinyLogic <sup>™</sup>      |
| E <sup>2</sup> CMOS <sup>™</sup>                 | HiSeC <sup>™</sup>              | MSXPro <sup>™</sup>            | Quiet Series <sup>™</sup>       | TruTranslation <sup>™</sup> |
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